Elektronische Bauelemente

BCP882H

3A , 70 V

NPN Plastic-Encapsulate Transistor

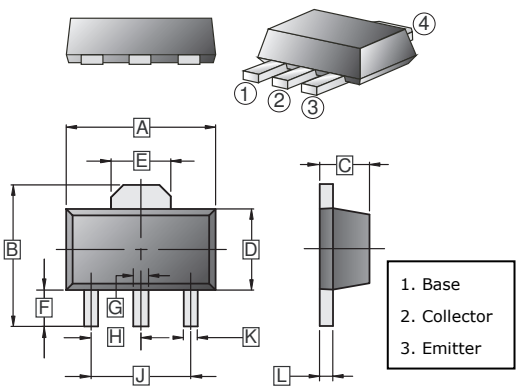
RoHS Compliant Product

A suffix of “-C” specifies halogen & lead-free

FEATURES

- Small Flat Package.
- High DC Current Gain
- Low $V_{CE(sat)}$

SOT-89



MARKING

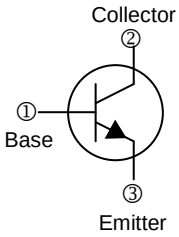
D882H

CLASSIFICATION OF h_{FE}

Rank	BCP882H-Y
Range	160~320

PACKAGE INFORMATION

Package	MPQ	Leader Size
SOT-89	1K	7 inch



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	4.40	4.60	G	0.40	0.58
B	3.94	4.25	H	1.50 TYP	
C	1.40	1.60	J	3.00 TYP	
D	2.25	2.60	K	0.32	0.52
E	1.55 TYP.		L	0.35	0.44
F	0.89	1.20			

ABSOLUTE MAXIMUM RATINGS (T_A=25℃ unless otherwise specified)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	70	V
Collector to Emitter Voltage	V_{CEO}	70	V
Emitter to Base Voltage	V_{EBO}	6	V
Continuous Collector Current	I_C	3	A
Collector Power Dissipation	P_C	500	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	250	℃ / W
Thermal Resistance Junction to Case	$R_{\theta JC}$	50	℃ / W
Junction, Storage Temperature	T_J, T_{STG}	150, -55~150	℃

ELECTRICAL CHARACTERISTICS (T_A=25℃ unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test condition
Collector to Base Breakdown Voltage	$V_{(BR)CBO}$	70	-	-	V	I_C=100μA, I_E=0
Collector to Emitter Breakdown Voltage	$V_{(BR)CEO}$	70	-	-	V	I_C=10mA, I_B=0
Emitter to Base Breakdown Voltage	$V_{(BR)EBO}$	6	-	-	V	I_E=100μA, I_C=0
Collector Cut-Off Current	I_{CBO}	-	-	1	μA	V_{CB}=40V, I_E=0
Collector cut-off current	I_{CEO}	-	-	10	μA	V_{CE}=30V, I_B=0
Emitter Cut-Off Current	I_{EBO}	-	-	1	μA	V_{EB}=6V, I_C=0
DC Current Gain	h_{FE}	160	-	320		V_{CE}=2V, I_C=1A
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	-	-	0.5	V	I_C=2A, I_B=0.2A
Base to emitter Saturation Voltage	$V_{BE(sat)}$	-	-	1.5	V	I_C=2A, I_B=0.2A
Transition Frequency	f_T	-	50	-	MHz	V_{CE}=5V, I_C=0.1A, f=10MHz

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CHARACTERISTIC CURVES